

SG2402TD

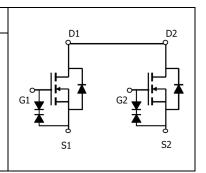
24V Common-Drain Dual N-Channel Power MOSFET

$$\begin{split} &V_{DSS}\,,\,24V \\ &R_{DS(ON)}\,,\,7.7\;m\Omega\;(max.)\;@\;V_{GS}{=}4.5V \\ &R_{DS(ON)}\,,\,7.9\;m\Omega\;(max.)\;@\;V_{GS}{=}4.0V \\ &R_{DS(ON)}\,,\,8.8\;m\Omega\;(max.)\;@\;V_{GS}{=}3.1V \end{split}$$

 $R_{DS(ON)}$, 9.8 m Ω (max.) @ V_{GS} =2.5V

I_D , 13A

DFN 3x3-8L



Description	Features
The SG2402TD uses advanced trench technology to provide excellent R _{DS(ON)} , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.	 Low On-Resistance ESD Protection Pb-free lead plating; RoHS compliant
No and processes.	Applications
	Load Switch
	Battery Powered Systems

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG2402TD	Halogen-Free	DFN 3x3-8L	TD	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

	Parameter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	24	V
Gate-Source Voltage		V _{GS}	±12	٧
Drain Current-Continuous	T _A =25°C	I _D	13	Α
Drain Current-Pulsed Note 1		I _{DM}	54	Α
Maximum Dawar Dissination	Mounted on ceramic substrate (900mm² x 0.8mm) 1 unit	P _D	2.7	W
Maximum Power Dissipation	Mounted on ceramic substrate (900mm² x 0.8mm)	PT	2.7	W
Operating Junction Temperature Range		TJ TSTG	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 1	Reja	Steady State	-	-	59	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	1.4	°C/W

Notes:

- 1. Pulse Test: Pulse Width ≤ 10µs, Duty Cycle ≤ 1%.
- 2. Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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24V Common-Drain Dual N-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

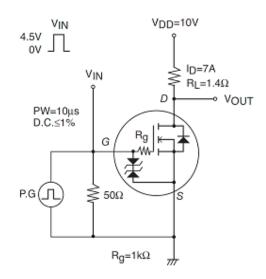
OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	24	27.5	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	I _{GSS}	$V_{GS}=\pm 8V$, $V_{DS}=0V$	-	-	±5	μA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	0.45	0.6	1.3	V
Drain -Source On -State Resistance		V _{GS} =4.5V, I _{DS} =5.5A	-	6.7	7.7	
		V _{GS} =4.0V, I _{DS} =5.5A	-	6.9	7.9	0
	R _{DS(ON)}	V _{GS} =3.1V, I _{DS} =5.5A	-	7.5	8.8	mΩ
		V _{GS} =2.5V, I _{DS} =3.0A	-	8.2	9.8	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	0.56	-	
Rise Time	t _r	V _{DD} =10V, I _{DS} =7A, V _{GS} =4.5V,	-	0.54	-]
Turn-Off Delay Time	T _{d(off)}	R_g =1K Ω See Switching Time Test Circuit		19	-	μs
Fall Time	t _f	- Coo Cwitching Time Tool Choole	-	22	-	
Total Gate Charge at 4.5V	Qg		-	13.2	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =10V, I _{DS} =13A, V _{GS} =4.5V	-	3.1	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	2.4	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter Symbol Conditions Min. Typ. Max. Unit				Unit		
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{DS} =13A	-	0.7	1.2	V

Switching Time Test Circuit



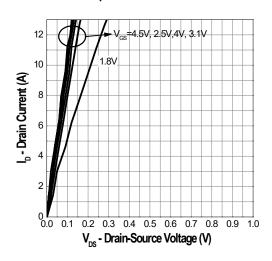




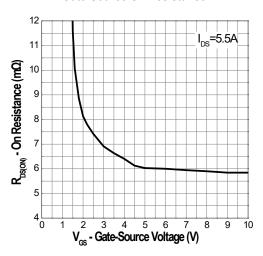
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Typical Operating Characteristics

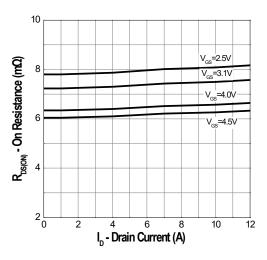
Output Characteristics



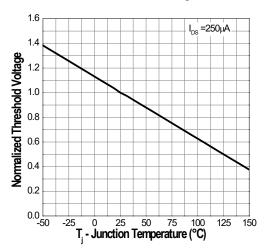
Gate-Source On Resistance



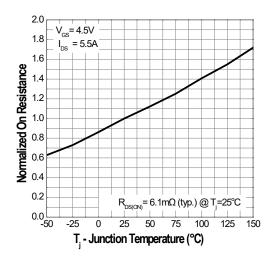
Drain-Source On Resistance



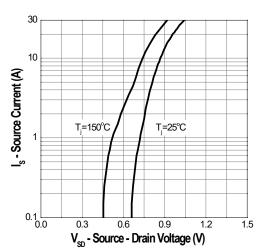
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward



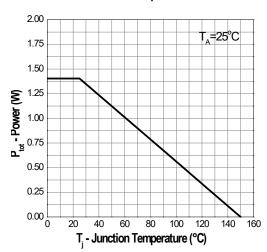




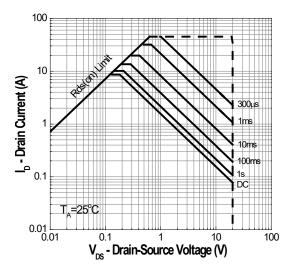
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Typical Operating Characteristics (Cont.)

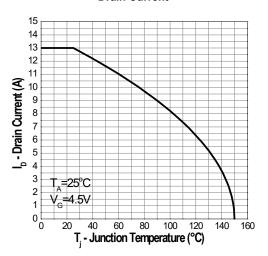
Power Dissipation



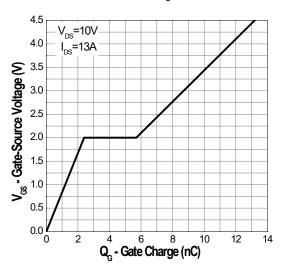
Safe Operation Area



Drain Current



Gate Charge



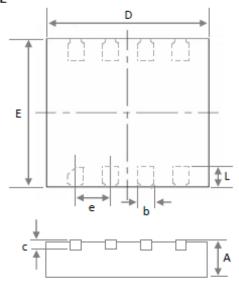




Package Dimensions

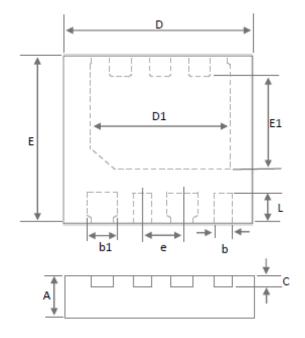
Package type: DFN3x3-8L

T-TYPE



Symbol	Min	Nor	Max
Α	0.70	0.75	0.80
b	0.25	0.30	0.35
С	0.15	0.20	0.25
D	2.90	3.00	3.10
E	2.90	3.00	3.10
е		0.65 BSC	,
L	0.37	0.51	0.65
b1	0.45	0.50	0.55
E1	1.625	1.725	1.825
D1	2.20	2.30	2.40
e1	0.425	0.525	0.625

S-TYPE



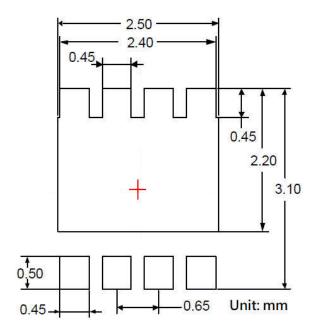
- 1. All dimension are in millimeters.
- 2. Dimension dose not include burrs and mold flash/protrusions.

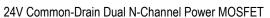


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Land pattern (Footprint)

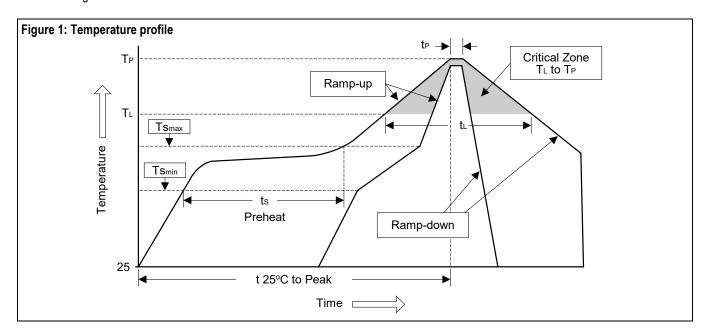






Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices

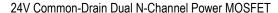


Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 oos	20 to 40 cos
Temperature (t⊳)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec







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